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   Nota di contenuto   Charge-based MOS Transistor Modeling; Contents; Foreword; Preface;
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                        Transistor Symbol and P-Channel Transistor; 3 The Basic Charge
                        Model; 3.1 Poisson's Equation and Gradual Channel Approximation; 3.2
                        Surface Potential as a Function of Gate Voltage
                        3.3 Gate Capacitance3.4 Charge Sheet Approximation; 3.5 Density of
                        Mobile Inverted Charge; 3.5.1 Mobile Charge as a Function of Gate
                        Voltage and Surface Potential; 3.5.2 Mobile Charge as a Function of
                        Channel Voltage and Surface Potential; 3.6 Charge-Potential
                        Linearization; 3.6.1 Linearization of Q_i (s); 3.6.2 Linearized Bulk
                        Depletion Charge Q_b; 3.6.3 Strong Inversion Approximation; 3.6.4
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Sommario/riassunto	Modern, large-scale analog integrated circuits (ICs) are essentially composed of metal-oxide semiconductor (MOS) transistors and their interconnections. As technology scales down to deep sub-micron dimensions and supply voltage decreases to reduce power consumption, these complex analog circuits are even more dependent on the exact behavior of each transistor. High-performance analog circuit design requires a very detailed model of the transistor, describing accurately its static and dynamic behaviors, its noise and matching limitations and its temperature variations. The charge-based EKV (Enz